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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

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Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	64
Program Memory Size	384КВ (384К х 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 17x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104mkafa-30

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

1.6 Outline of Functions

[30-pin, 32-pin, 36-pin, 40-pin products (code flash memory 16 KB to 64 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

		30-pin	32-pin	36-pin	(1/2 40-pin				
	Item	R5F104Ax (x = A, C to E)	R5F104Bx (x = A, C to E)	R5F104Cx (x = A, C to E)	R5F104Ex (x = A, C to E)				
Code flash mer	mory (KB)	16 to 64	16 to 64	16 to 64	16 to 64				
Data flash merr		4	4	4	4				
RAM (KB)		2.5 to 5.5 Note	2.5 to 5.5 Note	2.5 to 5.5 Note	2.5 to 5.5 Note				
Address space		1 MB	2.0 10 0.0	2.0 10 0.0	2.0 10 0.0				
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)							
	High-speed on-chip oscillator clock (fi⊣)	HS (high-speed main) mode: 1 to 32 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)							
Subsystem cloc	ck	— XT1 (crystal) oscillat external subsystem clock input (EXCLKS 32.768 kHz							
Low-speed on-o	chip oscillator clock	15 kHz (TYP.): VDD = 1.6 to 5.5 V							
General-purpos	se register	8 bits \times 32 registers (8 bits \times 8 registers \times 4 banks)							
Minimum instru	ction execution time	0.03125 μs (High-speed on-chip oscillator clock: fiH = 32 MHz operation)							
		$0.05\mu s$ (High-speed system	m clock: fmx = 20 MHz op	eration)					
		— 30.5 μs (Subsystem clock: fsuB = 32.768 kHz operation)							
Instruction set		 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits + 16 bits, 32 bits + 32 bits) Multiplication and Accumulation (16 bits × 16 bits + 32 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 							
I/O port	Total	26	28	32	36				
	CMOS I/O	21	22	26	28				
	CMOS input	3	3	3	5				
	CMOS output	_	_	—	-				
	N-ch open-drain I/O (6 V tolerance)	2	3	3					
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)							
	Watchdog timer	1 channel							
	Real-time clock (RTC)	1 channel							
	12-bit interval timer	1 channel							
	Timer output	Timer outputs: 13 channels PWM outputs: 9 channels							
	RTC output		1 • 1 Hz (subsystem clock: fsu = 32.768 kHz)						

(Note is listed on the next page.)



Note	The flash library uses RAM in self-programming and rewriting of the data flash memory.
	The target products and start address of the RAM areas used by the flash library are shown below.
	R5F104xD (x = A to C, E to G, J, L): Start address FE900H
	R5F104xE (x = A to C, E to G, J, L): Start address FE900H
	For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family
	(R20UT2944).



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		11 nin	10 nin	EQ nin	(2/2)				
	14	44-pin	48-pin	52-pin	64-pin				
	Item	R5F104Fx	R5F104Gx	R5F104Jx	R5F104Lx				
		(x = A, C to E)	(x = A, C to E)	(x = C to E)	(x = C to E)				
Clock output/buz	zer output	2	2	2	2				
			• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz						
			fmain = 20 MHz operatio						
		• 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz							
		(Subsystem clock: fs	uв = 32.768 kHz opera	tion)	1				
8/10-bit resolutio	n A/D converter	10 channels	10 channels	12 channels	12 channels				
Serial interface		• CSI: 1 channel/UAR	T (UART supporting LIN T: 1 channel/simplified I RT: 1 channel/simplified	² C: 1 channel	ified I ² C: 1 channel				
		[48-pin, 52-pin product	ts]						
		CSI: 2 channels/UAF	RT (UART supporting L	N-bus): 1 channel/simp	lified I ² C: 2 channels				
		CSI: 1 channel/UAR	T: 1 channel/simplified I	² C: 1 channel					
		CSI: 2 channels/UAF	RT: 1 channel/simplified	I ² C: 2 channels					
		[64-pin products]			_				
			RT (UART supporting L	, , ,	lified I ² C: 2 channels				
		CSI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels							
		CSI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels							
	I ² C bus	1 channel	1 channel	1 channel	1 channel				
Data transfer controller (DTC)		29 sources	30 sources		31 sources				
Event link contro	ller (ELC)	Event input: 20 Event trigger output: 7							
Vectored inter-	Internal	24	24	24	24				
rupt sources	External	7	10	12	13				
Key interrupt		4	6	8	8				
Reset Power-on-reset circuit		 Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution ^{Note} Internal reset by RAM parity error Internal reset by illegal-memory access 							
		• Power-on-reset: $1.51 \pm 0.04 \text{ V} (\text{TA} = -40 \text{ to } +85^{\circ}\text{C})$ $1.51 \pm 0.06 \text{ V} (\text{TA} = -40 \text{ to } +105^{\circ}\text{C})$ • Power-down-reset: $1.50 \pm 0.04 \text{ V} (\text{TA} = -40 \text{ to } +85^{\circ}\text{C})$ $1.50 \pm 0.06 \text{ V} (\text{TA} = -40 \text{ to } +105^{\circ}\text{C})$							
Voltage detector		1.63 V to 4.06 V (14 stages)							
On-chip debug fu	Inction	Provided							
Power supply vol	tage	VDD = 1.6 to 5.5 V (TA	= -40 to +85°C)						
		$V_{DD} = 2.4 \text{ to } 5.5 \text{ V} (T_A = -40 \text{ to } +105^{\circ}\text{C})$							
Operating ambie	nt temperature	$T_A = -40$ to +85°C (A: Consumer applications, D: Industrial applications), $T_A = -40$ to +105°C (G: Industrial applications)							

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

RENESAS

2. ELECTRICAL SPECIFICATIONS (TA = -40 to $+85^{\circ}$ C)

This chapter describes the following electrical specifications.

Target products A: Consumer applications $T_A = -40$ to $+85^{\circ}C$

R5F104xxAxx

- D: Industrial applications TA = -40 to +85°C R5F104xxDxx
- G: Industrial applications when TA = -40 to +105°C products is used in the range of TA = -40 to +85°C R5F104xxGxx
- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. With products not provided with an EVDD0, EVDD1, EVSS0, or EVSS1 pin, replace EVDD0 and EVDD1 with VDD, or replace EVSS0 and EVSS1 with VSS.
- Caution 3. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G14 User's Manual.



2.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operat-	HS (high-speed main)	fносо = 64 MHz,	Basic	V _{DD} = 5.0 V		2.4		mA
current		ing mode	mode Note 5	fiH = 32 MHz Note 3	operation	VDD = 3.0 V		2.4		
Note 1			fносо = 32 MHz,	Basic	VDD = 5.0 V		2.1			
				fiH = 32 MHz Note 3	operation	VDD = 3.0 V		2.1		
			HS (high-speed main)	fносо = 64 MHz,	Normal	VDD = 5.0 V		5.1	8.7	mA
		mode Note 5 fi	fiн = 32 MHz Note 3	operation	VDD = 3.0 V		5.1	8.7		
				fносо = 32 MHz,	Normal	VDD = 5.0 V		4.8	8.1	
			fiH = 32 MHz Note 3	operation	VDD = 3.0 V		4.8	8.1		
				fносо = 48 MHz,	Normal	VDD = 5.0 V		4.0	6.9	
			fiH = 24 MHz Note 3	operation	VDD = 3.0 V		4.0	6.9		
				fносо = 24 MHz,	Normal	VDD = 5.0 V		3.8	6.3	
				fiH = 24 MHz Note 3	operation	VDD = 3.0 V		3.8	6.3	
				fносо = 16 MHz,	Normal	VDD = 5.0 V		2.8	4.6	
				fiH = 16 MHz Note 3	operation	VDD = 3.0 V		2.8	4.6	
			LS (low-speed main)	fносо = 8 MHz,	Normal	VDD = 3.0 V		1.3	2.0	mA
			mode Note 5	fiH = 8 MHz Note 3	operation	VDD = 2.0 V		1.3	2.0	
			LV (low-voltage main)	fносо = 4 MHz,	Normal	VDD = 3.0 V		1.3	1.8	mA
		mode Note 5	fiH = 4 MHz Note 3	operation	VDD = 2.0 V		1.3	1.8		
	HS (high-speed main) mode ^{Note 5}	f _{MX} = 20 MHz ^{Note 2} , V _{DD} = 5.0 V	Normal operation	Square wave input		3.3	5.3	mA		
				Resonator connection		3.4	5.5	1		
			1	fmx = 20 MHz Note 2,	Normal operation	Square wave input		3.3	5.3	
				VDD = 3.0 V		Resonator connection		3.4	5.5	
			f _{MX} = 10 MHz ^{Note 2} ,	Normal	Square wave input		2.0	3.1	1	
				VDD = 5.0 V	operation	Resonator connection		2.1	3.2	1
			f _{MX} = 10 MHz ^{Note 2} ,	Normal	Square wave input		2.0	3.1	1	
				VDD = 3.0 V	operation	Resonator connection		2.1	3.2	1
			LS (low-speed main)	f _{MX} = 8 MHz Note 2,	Normal	Square wave input		1.2	1.9	mA
		mode Note 5	VDD = 3.0 V	operation	Resonator connection		1.2	2.0		
				fmx = 8 MHz Note 2,	Normal	Square wave input		1.2	1.9	
				VDD = 2.0 V	operation	Resonator connection		1.2	2.0	
			Subsystem clock	fsue = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	μA
			operation	TA = -40°C	operation	Resonator connection		4.7	6.1	
				fsue = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	
				TA = +25°C	operation	Resonator connection		4.7	6.1	
		fsue = 32.768 kHz Note 4	Normal	Square wave input		4.8	6.7	1		
				TA = +50°C	operation	Resonator connection	1	4.8	6.7	
				fsue = 32.768 kHz Note 4	Normal	Square wave input		4.8	7.5	1
				TA = +70°C	operation	Resonator connection		4.8	7.5	1
				fsue = 32.768 kHz Note 4	Normal	Square wave input		5.4	8.9	1
				TA = +85°C	operation	Resonator connection		5.4	8.9	1

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3. When high-speed system clock and subsystem clock are stopped.
- Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:	$2.7~V \leq V_{DD} \leq 5.5~V@1~MHz$ to 32 MHz
	2.4 V \leq VDD \leq 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode:	1.8 V \leq VDD \leq 5.5 V@1 MHz to 8 MHz
LV (low-voltage main) mode:	1.6 V \leq VDD \leq 5.5 V@1 MHz to 4 MHz

- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.) Remark 3. file:
- High-speed on-chip oscillator clock frequency (32 MHz max.) Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

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(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

Parameter	Symbol	Conditions		Conditions HS (high-speed main) L mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		reception	$\begin{array}{l} 4.0 \; V \leq E V_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V \end{array}$		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		fMCK/6 Note 1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 4$		5.3		1.3		0.6	Mbps
			$2.7 V \le EV_{DD0} < 4.0 V,$ $2.3 V \le V_b \le 2.7 V$		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 4$		5.3		1.3		0.6	Mbps
			$1.8 V \le EV_{DD0} < 3.3 V,$ $1.6 V \le V_b \le 2.0 V$		fмск/6 Notes 1, 2, 3		fмск/6 Notes 1, 2		fмск/6 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 4		5.3		1.3		0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. Use it with $EV_{DD0} \ge V_b$.

Note 3.The following conditions are required for low voltage interface when EVDD0 < VDD. $2.4 V \le EVDD0 < 2.7 V$: MAX. 2.6 Mbps $1.8 V \le EVDD0 < 2.4 V$: MAX. 1.3 Mbps

Note 4. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

HS (high-speed main) mode:	32 MHz (2.7 V \leq VDD \leq 5.5 V)
	16 MHz (2.4 V \leq VDD \leq 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V \leq VDD \leq 5.5 V)
LV (low-voltage main) mode:	4 MHz (1.6 V \leq VDD \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

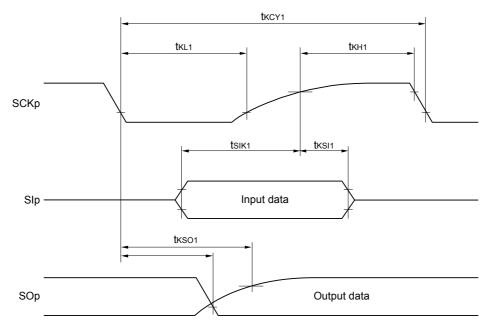
Remark 1. Vb [V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

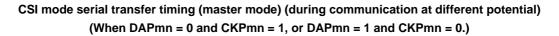
Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

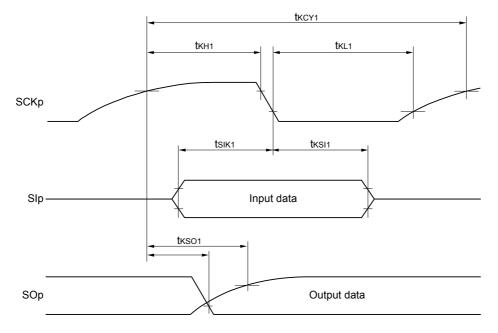
Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.





CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





- Remark 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)
- Remark 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1/fмск + 135 Note 3		1/fmck + 190 Note 3		1/fмск + 190 Note 3		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/fмск + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		ns
		$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_{b} \leq 4.0 \; V, \\ C_{b} = 100 \; pF, \; R_{b} = 2.8 \; k\Omega \end{array}$	1/fмск + 190 Note 3		1/fmck + 190 Note 3		1/fмск + 190 Note 3		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/fмск + 190 Note 3		1/fmck + 190 Note 3		1/f _{MCK} + 190 Note 3		ns
		$\begin{array}{l} 1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ 1.6 \; V \leq V_{b} \leq 2.0 \; V \; ^{Note 2}, \\ C_{b} = 100 \; pF, \; R_{b} = 5.5 \; k\Omega \end{array}$	1/fмск + 190 Note 3		1/fmck + 190 Note 3		1/fмск + 190 Note 3		ns
Data hold time tHD: (transmission)	thd:dat	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	305	0	305	0	305	ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	0	305	0	305	0	305	ns
			0	355	0	355	0	355	ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	355	0	355	0	355	ns
		$ \begin{split} & 1.8 \; \text{V} \leq \text{EV}_{\text{DD0}} < 3.3 \; \text{V}, \\ & 1.6 \; \text{V} \leq \text{V}_{b} \leq 2.0 \; \text{V} \; ^{\text{Note 2}}, \\ & \text{C}_{b} = 100 \; \text{pF}, \; \text{R}_{b} = 5.5 \; \text{k}\Omega \end{split} $	0	405	0	405	0	405	ns

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

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Note 1. The value must also be equal to or less than fmck/4.

Note 2. Use it with $EV_{DD0} \ge V_b$.

Note 3. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)



(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI14, ANI16 to ANI20, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$1.8~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$		1.2	±7.0	LSB
			1.6 V \leq VDD \leq 5.5 V Note 3		1.2	±10.5	LSB
Conversion time	tconv	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin: ANI0 to ANI14, ANI16 to ANI20	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.1875		39	μs
			$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
			$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	57		95	μs
		10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.375		39	μs
		Target pin: internal reference voltage, and temperature sensor output voltage	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.5625		39	μs
		(HS (high-speed main) mode)	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
		1	$1.6~V \leq V_{DD} \leq 5.5~V~\text{Note}~3$			±0.85	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
			1.6 V \leq VDD \leq 5.5 V Note 3			±0.85	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			±4.0	LSB
			$1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$ Note 3			±6.5	LSB
Differential linearity error	DLE	10-bit resolution	$1.8~\text{V} \leq \text{V}_\text{DD} \leq 5.5~\text{V}$			±2.0	LSB
Note 1			$1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$ Note 3			±2.5	LSB
Analog input voltage	VAIN	ANI0 to ANI14		0		Vdd	V
		ANI16 to ANI20		0		EV _{DD0}	V
		Internal reference voltage (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) r	node)	١	/BGR Note	4	V
		Temperature sensor output voltage (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) r	node)	Vī	MPS25 Not	te 4	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. When the conversion time is set to 57 μ s (min.) and 95 μ s (max.).

Note 4. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



RL78/G14

2.6.2 Temperature sensor characteristics/internal reference voltage characteristic

	-					
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	Vbgr	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V, HS (high-speed main) mode)

2.6.3 D/A converter characteristics

(TA = -40 to +85°C, 1.6 V \leq EVsso = EVss1 \leq VDD \leq 5.5 V, Vss = EVsso = EVss1 = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 M Ω	$1.8~V \le V \text{DD} \le 5.5~V$			±2.5	LSB
		Rload = 8 M Ω	$1.8~V \le V_{DD} \le 5.5~V$			±2.5	LSB
Settling time	t SET	Cload = 20 pF	$2.7~V \leq V_{DD} \leq 5.5~V$			3	μs
			$1.6~V \leq V_{DD} < 2.7~V$			6	μs



Interrupt Request Input Timing INTPO to INTP11 Key Interrupt Input Timing KR0 to KR7 RESET Input Timing

RESET



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) (TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Symbol Conditions			HS (high-speed main) mode	
				MIN.	MAX.	
SCKp cycle time	tксү1	tkcy1 ≥ 4/fclk	$2.7 \text{ V} \leq \text{Evdd0} \leq 5.5 \text{ V}$	250		ns
			$2.4~\text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5~\text{V}$	500		ns
SCKp high-/low-level width	tĸнı, tĸ∟ı	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}}$	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		tксү1/2 - 36		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		tксү1/2 - 76		ns
SIp setup time (to SCKp [↑]) Note 1	tsiĸ1	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}}$	≤ 5.5 V	66		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}}$	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		113		ns
SIp hold time (from SCKp↑) Note 2	tĸsı1			38		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Note 4			50	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)
- Remark 2. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

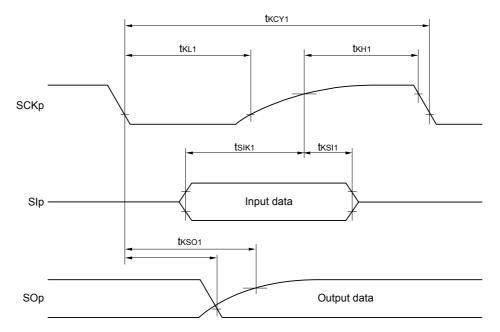
Parameter	Symbol	C	onditions	HS (high-speed	main) mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1 tkcy1 ≥ 4/fclk			600		ns
			$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1000		ns
			$\begin{array}{l} 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	2300		ns
SCKp high-level width	tкнı			tĸcy1/2 - 150		ns
				tксү1/2 - 340		ns
	$\begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$,	tксү1/2 - 916		ns
SCKp low-level width	tKL1	$2.7~V \leq V_b \leq 4.0~V,$	4.0 V \leq EV _{DD0} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ			ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \end{array}$,	tксү1/2 - 36		ns
		$\begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \end{array}$,	tkcy1/2 - 100		ns

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

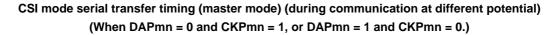
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

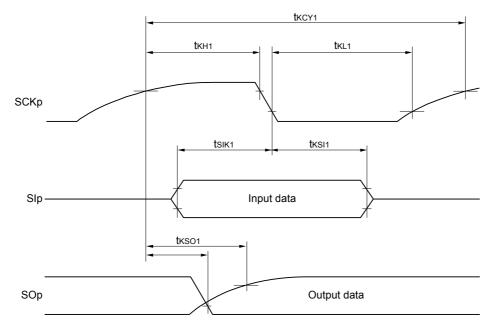
(**Remarks** are listed two pages after the next page.)





CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





- Remark 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)
- Remark 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage Input channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = V _{DD} Reference voltage (-) = V _{SS}	Reference voltage (+) = VBGR Reference voltage (-)= AVREFM
ANI0 to ANI14	Refer to 3.6.1 (1).	Refer to 3.6.1 (3).	Refer to 3.6.1 (4).
ANI16 to ANI20	Refer to 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1) .		_

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution AV _{REFP} = V _{DD} Note 3	$2.4~V \leq AV_{REFP} \leq 5.5~V$		1.2	±3.5	LSB
Conversion time	tCONV	10-bit resolution	$3.6~V \le V_{DD} \le 5.5~V$	2.125		39	μs
		Target pin: ANI2 to ANI14	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.1875		39	μs
			$2.4~V \le V_{DD} \le 5.5~V$	17		39	μs
		10-bit resolution	$3.6~V \le V_{DD} \le 5.5~V$	2.375		39	μs
		Target pin: Internal reference voltage, and temperature sensor output volt-	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.5625		39	μs
		age (HS (high-speed main) mode)	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution AV _{REFP} = V _{DD} Note 3	$2.4 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			±0.25	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution AV _{REFP} = V _{DD} Note 3	$2.4~V \leq AV_{REFP} \leq 5.5~V$			±0.25	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AV _{REFP} = V _{DD} Note 3	$2.4~V \le AV_{REFP} \le 5.5~V$			±2.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV _{REFP} = V _{DD} Note 3	$2.4 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			±1.5	LSB
Analog input voltage	VAIN	ANI2 to ANI14		0		AVREFP	V
		Internal reference voltage output (2.4 V \leq VDD \leq 5.5 V, HS (high-speed n	nain) mode)	\	/ _{BGR} Note	4	V
		Temperature sensor output voltage (2.4 V \leq VDD \leq 5.5 V, HS (high-speed n	nain) mode)	V _{TMPS25} Note		te 4	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

 Note 3.
 When AVREFP < VDD, the MAX. values are as follows.</th>

 Overall error:
 Add ±1.0 LSB to the MAX. value when AVREFP = VDD.

 Zero-scale error/Full-scale error:
 Add ±0.05%FSR to the MAX. value when AVREFP = VDD.

 Integral linearity error/ Differential linearity error:
 Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

 Note 4.
 Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 to ANI14, ANI16 to ANI20

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, 1.6 V \leq EVDD = EVDD1 \leq VDD, Vss = EVss0 = EVss1 = 0 V,

Reference voltage (+) = VBGR Note 3, Reference voltage (-) = AVREFM = 0 V Note 4, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit	
Conversion time	tCONV	8-bit resolution	$2.4~\text{V} \leq \text{V}\text{DD} \leq 5.5~\text{V}$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	% FSR
Integral linearity error Note 1	ILE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±1.0	LSB
Analog input voltage	VAIN			0		VBGR Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

Note 4. When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error:Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.Integral linearity error:Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.Differential linearity error:Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

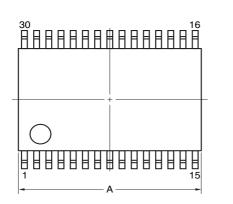


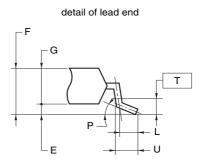
4. PACKAGE DRAWINGS

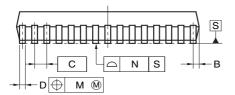
4.1 30-pin products

R5F104AAASP, R5F104ACASP, R5F104ADASP, R5F104AEASP, R5F104AFASP, R5F104AGASP R5F104AADSP, R5F104ACDSP, R5F104ADDSP, R5F104AEDSP, R5F104AFDSP, R5F104AGDSP R5F104AAGSP, R5F104ACGSP, R5F104ADGSP, R5F104AEGSP, R5F104AFGSP, R5F104AGGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18

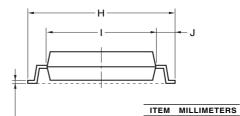






NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.



·κ

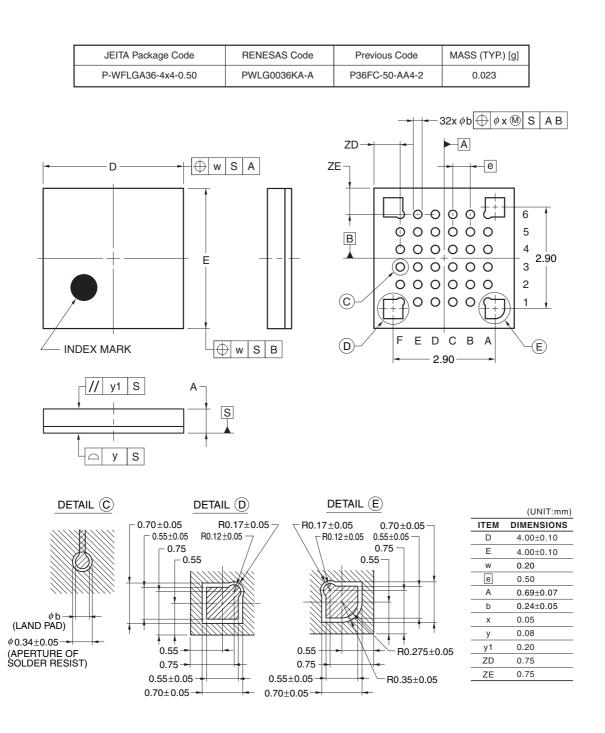
Α 9.85±0.15 в 0.45 MAX С 0.65 (T.P.) $0.24_{-0.07}^{+0.08}$ D F 0.1±0.05 F 1.3±0.1 G 1.2 8.1±0.2 Н 6.1±0.2 I 1.0±0.2 J 0.17±0.03 κ L 0.5 0.13 Μ Ν 0.10 Р 3°+5° 0.25 т 0.6±0.15 U

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4.3 36-pin products

R5F104CAALA, R5F104CCALA, R5F104CDALA, R5F104CEALA, R5F104CFALA, R5F104CGALA R5F104CAGLA, R5F104CCGLA, R5F104CDGLA, R5F104CEGLA, R5F104CFGLA, R5F104CGGLA



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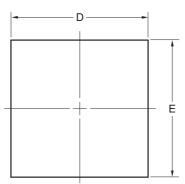
4.4 40-pin products

R5F104EAANA, R5F104ECANA, R5F104EDANA, R5F104EEANA, R5F104EFANA, R5F104EGANA, R5F104EHANA

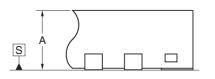
R5F104EADNA, R5F104ECDNA, R5F104EDDNA, R5F104EEDNA, R5F104EFDNA, R5F104EGDNA, R5F104EHDNA

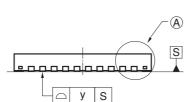
R5F104EAGNA, R5F104ECGNA, R5F104EDGNA, R5F104EEGNA, R5F104EFGNA, R5F104EGGNA, R5F104EHGNA

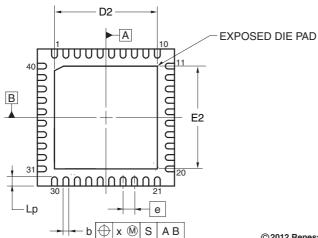
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN40-6x6-0.50	PWQN0040KC-A	P40K8-50-4B4-4	0.09











Referance	Dimens	sion in Mill	imeters
Symbol	Min	Nom	Max
D	5.95	6.00	6.05
E	5.95	6.00	6.05
А	0.70	0.75	0.80
b	0.18	0.25	0.30
е		0.50	—
Lp	0.30	0.40	0.50
х		—	0.05
У			0.05

ITEM			D2			E2	
		MIN	NOM	MAX	MIN	NOM	MAX
EXPOSED DIE PAD VARIATIONS	А	4.45	4.50	4.55	4.45	4.50	4.55

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